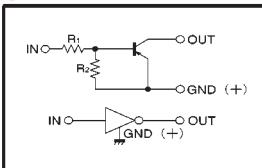


Digital transistors (built-in resistors)

DTA115EE / DTA115EUA / DTA115EKA / DTA115ESA

●Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- The bias resistors consist of thin-film resistors with complete isolation to allow positive biasing of the input, and parasitic effects are almost completely eliminated.
- Only the on / off conditions need to be set for operation, making device design easy.
- Higher mounting densities can be achieved.

●Circuit schematic**●Electrical characteristics (Ta=25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{(off)}$	—	—	-0.5	V	$V_{cc} = -5V, I_o = -100\mu A$
	$V_{(on)}$	-3	—	—	V	$V_o = -0.3V, I_o = -1mA$
Output voltage	$V_{O(on)}$	—	-0.1	-0.3	V	$I_o = -5mA, I_i = -0.25mA$
Input current	I_i	—	—	-0.15	mA	$V_i = -5V$
Output current	$I_{O(off)}$	—	—	-0.5	μA	$V_{cc} = -50V, V_i = 0V$
DC current gain	G_i	82	—	—	—	$I_o = -5mA, V_o = -5V$
Input resistance	R_1	70	100	130	k Ω	—
Resistance ratio	R_2/R_1	0.8	1	1.2	—	—
Transition frequency	f_T	—	250	—	MHz	$V_{ce} = 10V, I_e = -5mA, f = 100MHz$ *

* Transition frequency of the device.

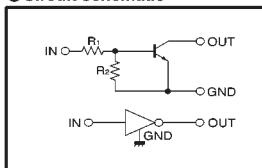
(94S-522-A115E)

Digital transistors (built-in resistors)

DTC115EE / DTC115EUA / DTC115EKA / DTC115ESA

●Features

- Built-in bias resistors enable the configuration of an inverter circuit without connecting external input resistors.
- The bias resistors consist of thin-film resistors with complete isolation to allow negative biasing of the input, and parasitic effects are almost completely eliminated.
- Only the on / off conditions need to be set for operation, making device design easy.
- Higher mounting densities can be achieved.

●Circuit schematic**●Electrical characteristics (Ta=25°C)**

Parameter	Symbol	Min.	Typ.	Max.	Unit	Conditions
Input voltage	$V_{(off)}$	—	—	0.5	V	$V_{cc} = 5V, I_o = 100\mu A$
	$V_{(on)}$	3	—	—	V	$V_o = 0.3V, I_o = 1mA$
Output voltage	$V_{O(on)}$	—	0.1	0.3	V	$I_o = 5mA, I_i = 0.25mA$
Input current	I_i	—	—	0.15	mA	$V_i = 5V$
Output current	$I_{O(off)}$	—	—	0.5	μA	$V_{cc} = 50V, V_i = 0V$
DC current gain	G_i	82	—	—	—	$I_o = 5mA, V_o = 5V$
Input resistance	R_1	70	100	130	k Ω	—
Resistance ratio	R_2/R_1	0.8	1	1.2	—	—
Transition frequency	f_T	—	250	—	MHz	$V_{ce} = 10V, I_e = -5mA, f = 100MHz$ *

* Transition frequency of the device.

(94S-644-C115E)